



# 4/A

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Mullish

PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Trivedi et al.

Appl. No. : 10/038,305

Filed : January 2, 2002

For : METHOD OF FORMING A  
DUAL DAMASCENE  
INTERCONNECT (As  
Amended Herewith)

Examiner : T. Nguyen

Group Art Unit 2813

I hereby certify that this correspondence and all  
marked attachments are being deposited with the  
United States Postal Service as first-class mail in  
an envelope addressed to: United States Patent  
and Trademark Office, P.O. Box 2327,  
Arlington, VA 22202, on

November 20, 2002

(Date)

Adeel S. Akhtar

Adeel S. Akhtar, Reg. No. 41,394

AMENDMENT AND RESPONSE TO OFFICE ACTIONUnited States Patent and Trademark Office  
P.O. Box 2327  
Arlington, VA 22202

Dear Sir:

In response to the Office Action mailed on August 28, 2002, please amend the above-captioned application as follows:

IN THE SPECIFICATION:

Please amend the title paragraph beginning on page 1, line 2 as follows:

METHOD OF FORMING A DUAL DAMASCENE INTERCONNECT

IN THE CLAIMS:

Please amend the following claim:

SUBC17  
AI  
11. (Amended) A method for fabricating an integrated circuit interconnect  
structure, comprising:etching a pattern of dual damascene trenches and contact vias in insulating  
material;preferentially depositing a first metal into the contact vias to partially fill the  
contact vias; and